

Complementary Enhancement-Mode Vertical DMOS Power FETs Quad Array

Ordering Information

BV _{DSS} / BV _{DGS}	R _{DS(ON)} Max Q ₁ + Q ₂ or Q ₃ + Q ₄	Order Number / Package
		SOW-20*
40V	2.75Ω	TC0604WG

*Same as SO-20 with 300 mil wide body.

Features

- 4 independent channels
- 4 electrically isolated die
- Commercial and Military versions available
- Freedom from secondary breakdown
- Low power drive requirement
- Low C_{ISS} and fast switching speeds
- High input impedance and high gain
- Complementary N- and P-Channel devices

Applications

- Motor control
- Convertors
- Amplifiers
- Switches
- Power supply circuits
- Driver (Relays, Hammers, Solenoids, Lamps, Memories, Displays, Bipolar Transistors, etc.)

Thermal Characteristics

Package	Plastic SOW-20	
I _D continuous & I _{DR} (single die)	N-Channel	1.0A
	P-Channel	0.6A
I _D pulsed* & I _{DRM} †	N-Channel	4.0A
	P-Channel	2.0A
Power Dissipation @ T _C = 25°C†	1.5W	
θ _{ja} (°C/W)	85	
θ _{jc} (°C/W)	—	

* Pulse test 300 μS pulse, 2% duty cycle.

† Total for package.

Advanced DMOS Technology

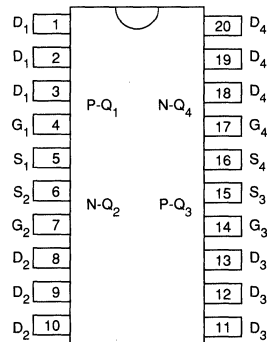
These enhancement-mode (normally-off) power transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and negative temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

Supertex Vertical DMOS Power FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Electrical Characteristics

Refer to TN06L and TP06L Data Sheets for detailed characteristics of N- and P-channel devices.

Pin Configuration



top view

SOW-20